

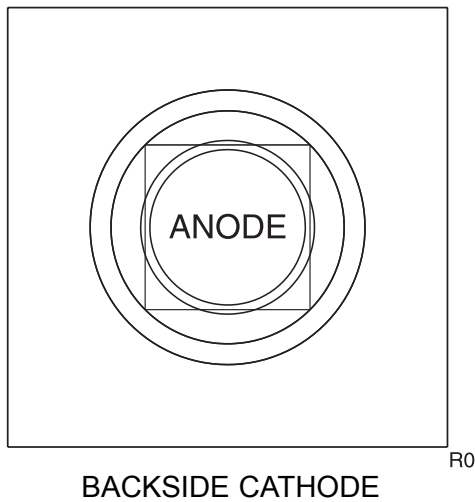
PROCESS CPD41
Switching Diode
High Current Switching Diode Chip

CentralTM
Semiconductor Corp.

PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	20 x 20 MILS
Die Thickness	8.0 MILS
Anode Bonding Pad Area	6.5 x 6.5 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au - 12,000Å

GEOMETRY



GROSS DIE PER 4 INCH WAFER

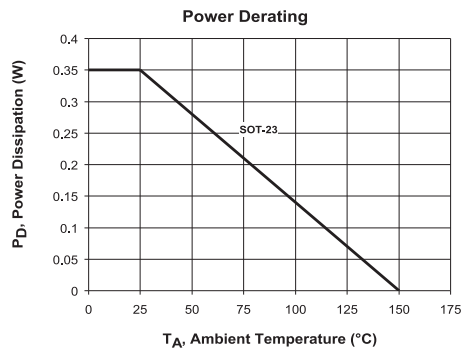
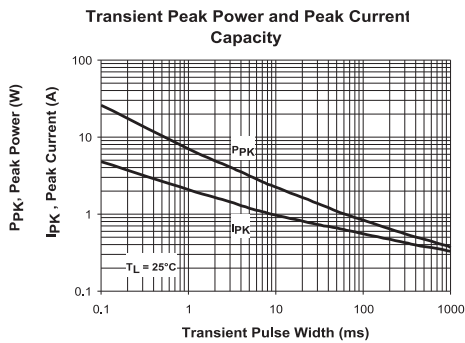
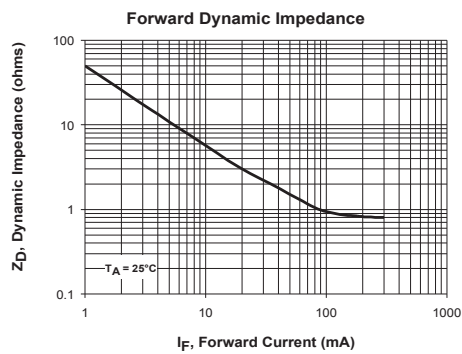
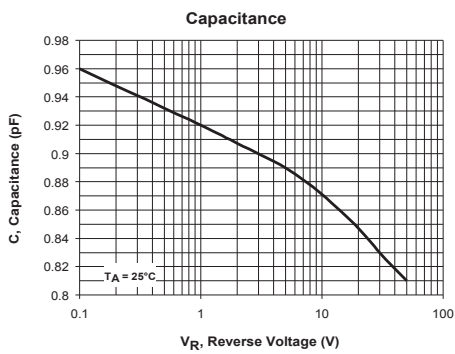
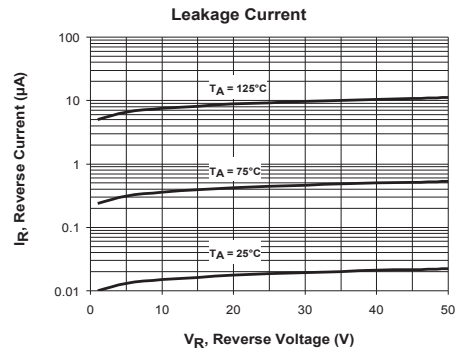
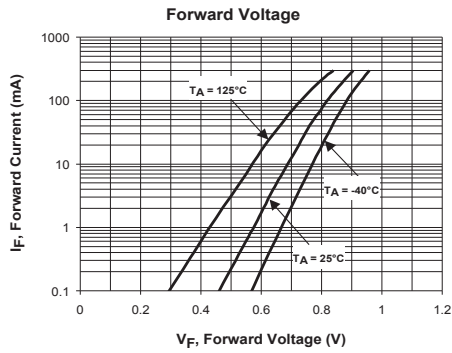
29,250

PRINCIPAL DEVICE TYPES

1N3600
1N4150
CMPD4150

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R2 (1-August 2002)



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